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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I ² C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, CapSense, LCD, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x10b Slope, 16x12b SAR; D/A 2xIDAC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	35-XFBGA, WLCSP
Supplier Device Package	35-WLCSP (2.58x2.1)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4124fni-s433t



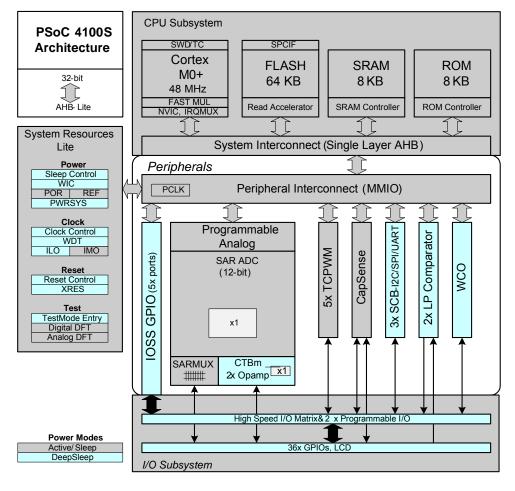


Figure 1. Block Diagram

PSoC 4100S devices include extensive support for programming, testing, debugging, and tracing both hardware and firmware.

The ARM Serial-Wire Debug (SWD) interface supports all programming and debug features of the device.

Complete debug-on-chip functionality enables full-device debugging in the final system using the standard production device. It does not require special interfaces, debugging pods, simulators, or emulators. Only the standard programming connections are required to fully support debug.

The PSoC Creator IDE provides fully integrated programming and debug support for the PSoC 4100S devices. The SWD interface is fully compatible with industry-standard third-party tools. The PSoC 4100S family provides a level of security not possible with multi-chip application solutions or with microcontrollers. It has the following advantages:

- Allows disabling of debug features
- Robust flash protection
- Allows customer-proprietary functionality to be implemented in on-chip programmable blocks

The debug circuits are enabled by default and can be disabled in firmware. If they are not enabled, the only way to re-enable them is to erase the entire device, clear flash protection, and reprogram the device with new firmware that enables debugging. Thus firmware control of debugging cannot be over-ridden without erasing the firmware thus providing security.

Additionally, all device interfaces can be permanently disabled (device security) for applications concerned about phishing attacks due to a maliciously reprogrammed device or attempts to defeat security by starting and interrupting flash programming sequences. All programming, debug, and test interfaces are disabled when maximum device security is enabled. Therefore, PSoC 4100S, with device security enabled, may not be returned for failure analysis. This is a trade-off the PSoC 4100S allows the customer to make.



supports EZI2C that creates a mailbox address range in the memory of the PSoC 4100S and effectively reduces I²C communication to reading from and writing to an array in memory. In addition, the block supports an 8-deep FIFO for receive and transmit which, by increasing the time given for the CPU to read data, greatly reduces the need for clock stretching caused by the CPU not having read data on time.

The I^2C peripheral is compatible with the I^2C Standard-mode and Fast-mode devices as defined in the NXP I^2C -bus specification and user manual (UM10204). The I^2C bus I/O is implemented with GPIO in open-drain modes.

The PSoC 4100S is not completely compliant with the I²C spec in the following respect:

■ GPIO cells are not overvoltage tolerant and, therefore, cannot be hot-swapped or powered up independently of the rest of the I²C system.

UART Mode: This is a full-feature UART operating at up to 1 Mbps. It supports automotive single-wire interface (LIN), infrared interface (IrDA), and SmartCard (ISO7816) protocols, all of which are minor variants of the basic UART protocol. In addition, it supports the 9-bit multiprocessor mode that allows addressing of peripherals connected over common RX and TX lines. Common UART functions such as parity error, break detect, and frame error are supported. An 8-deep FIFO allows much greater CPU service latencies to be tolerated.

SPI Mode: The SPI mode supports full Motorola SPI, TI SSP (adds a start pulse used to synchronize SPI Codecs), and National Microwire (half-duplex form of SPI). The SPI block can use the FIFO.

GPIO

The PSoC 4100S has up to 36 GPIOs. The GPIO block implements the following:

- Eight drive modes:
 - ☐ Analog input mode (input and output buffers disabled)
 - □ Input only
 - ☐ Weak pull-up with strong pull-down
 - ☐ Strong pull-up with weak pull-down
 - □ Open drain with strong pull-down
 - □ Open drain with strong pull-up
 - $\ensuremath{\square}$ Strong pull-up with strong pull-down
 - □ Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL).
- Individual control of input and output buffer enabling/disabling in addition to the drive strength modes
- Selectable slew rates for dV/dt related noise control to improve EMI

The pins are organized in logical entities called ports, which are 8-bit in width (less for Ports 2 and 3). During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix is used to multiplex between various signals that may connect to an I/O pin.

Data output and pin state registers store, respectively, the values to be driven on the pins and the states of the pins themselves.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it (5 for PSoC 4100S).

Special Function Peripherals

CapSense

CapSense is supported in the PSoC 4100S through a CapSense Sigma-Delta (CSD) block that can be connected to any pins through an analog multiplex bus via analog switches. CapSense function can thus be provided on any available pin or group of pins in a system under software control. A PSoC Creator component is provided for the CapSense block to make it easy for the user.

Shield voltage can be driven on another analog multiplex bus to provide water-tolerance capability. Water tolerance is provided by driving the shield electrode in phase with the sense electrode to keep the shield capacitance from attenuating the sensed input. Proximity sensing can also be implemented.

The CapSense block has two IDACs, which can be used for general purposes if CapSense is not being used (both IDACs are available in that case) or if CapSense is used without water tolerance (one IDAC is available).

The CapSense block also provides a 10-bit Slope ADC function which can be used in conjunction with the CapSense function.

The CapSense block is an advanced, low-noise, programmable block with programmable voltage references and current source ranges for improved sensitivity and flexibility. It can also use an external reference voltage. It has a full-wave CSD mode that alternates sensing to VDDA and ground to null out power-supply related noise.

LCD Segment Drive

The PSoC 4100S has an LCD controller, which can drive up to 4 commons and up to 32 segments. It uses full digital methods to drive the LCD segments requiring no generation of internal LCD voltages. The two methods used are referred to as Digital Correlation and PWM. Digital Correlation pertains to modulating the frequency and drive levels of the common and segment signals to generate the highest RMS voltage across a segment to light it up or to keep the RMS signal to zero. This method is good for STN displays but may result in reduced contrast with TN (cheaper) displays. PWM pertains to driving the panel with PWM signals to effectively use the capacitance of the panel to provide the integration of the modulated pulse-width to generate the desired LCD voltage. This method results in higher power consumption but can result in better results when driving TN displays. LCD operation is supported during Deep Sleep refreshing a small display buffer (4 bits; 1 32-bit register per port).



Pinouts

The following table provides the pin list for PSoC 4100S for the 48-pin TQFP, 44-pin TQFP, 40-pin QFN, 32-pin QFN, and 35-ball CSP packages. All port pins support GPIO.

Table 1. Pin List

48-1	TQFP	44-	TQFP	40	-QFN	32	-QFN	35	5-CSP
Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
28	P0.0	24	P0.0	22	P0.0	17	P0.0	C3	P0.0
29	P0.1	25	P0.1	23	P0.1	18	P0.1	A5	P0.1
30	P0.2	26	P0.2	24	P0.2	19	P0.2	A4	P0.2
31	P0.3	27	P0.3	25	P0.3	20	P0.3	A3	P0.3
32	P0.4	28	P0.4	26	P0.4	21	P0.4	В3	P0.4
33	P0.5	29	P0.5	27	P0.5	22	P0.5	A6	P0.5
34	P0.6	30	P0.6	28	P0.6	23	P0.6	B4	P0.6
35	P0.7	31	P0.7	29	P0.7			B5	P0.7
36	XRES	32	XRES	30	XRES	24	XRES	В6	XRES
37	VCCD	33	VCCD	31	VCCD	25	VCCD	A7	VCCD
38	VSSD			DN	VSSD	26	VSSD	В7	VSS
39	VDDD	34	VDDD	32	VDDD			C7	VDD
40	VDDA	35	VDDA	33	VDDA	27	VDD	C7	VDD
41	VSSA	36	VSSA	34	VSSA	28	VSSA	В7	VSS
42	P1.0	37	P1.0	35	P1.0	29	P1.0	C4	P1.0
43	P1.1	38	P1.1	36	P1.1	30	P1.1	C5	P1.1
44	P1.2	39	P1.2	37	P1.2	31	P1.2	C6	P1.2
45	P1.3	40	P1.3	38	P1.3	32	P1.3	D7	P1.3
46	P1.4	41	P1.4	39	P1.4			D4	P1.4
47	P1.5	42	P1.5					D5	P1.5
48	P1.6	43	P1.6					D6	P1.6
1	P1.7/VREF	44	P1.7/VREF	40	P1.7/VREF	1	P1.7/VREF	E7	P1.7/VRE
		1	VSSD						
2	P2.0	2	P2.0	1	P2.0	2	P2.0		
3	P2.1	3	P2.1	2	P2.1	3	P2.1		
4	P2.2	4	P2.2	3	P2.2	4	P2.2	D3	P2.2
5	P2.3	5	P2.3	4	P2.3	5	P2.3	E4	P2.3
6	P2.4	6	P2.4	5	P2.4			E5	P2.4
7	P2.5	7	P2.5	6	P2.5	6	P2.5	E6	P2.5
8	P2.6	8	P2.6	7	P2.6	7	P2.6	E3	P2.6
9	P2.7	9	P2.7	8	P2.7	8	P2.7	E2	P2.7
10	VSSD	10	VSSD	9	VSSD		1		
12	P3.0	11	P3.0	10	P3.0	9	P3.0	E1	P3.0
13	P3.1	12	P3.1	11	P3.1	10	P3.1	D2	P3.1
14	P3.2	13	P3.2	12	P3.2	11	P3.2	D1	P3.2
16	P3.3	14	P3.3	13	P3.3	12	P3.3	C1	P3.3
17	P3.4	15	P3.4	14	P3.4			C2	P3.4
18	P3.5	16	P3.5	15	P3.5				



Table 1. Pin List (continued)

48-T	QFP	44-T	QFP	40-0	QFN	32-QFN		35-	CSP
Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
19	P3.6	17	P3.6	16	P3.6				
20	P3.7	18	P3.7	17	P3.7				
21	VDDD	19	VDDD						
22	P4.0	20	P4.0	18	P4.0	13	P4.0	B1	P4.0
23	P4.1	21	P4.1	19	P4.1	14	P4.1	B2	P4.1
24	P4.2	22	P4.2	20	P4.2	15	P4.2	A2	P4.2
25	P4.3	23	P4.3	21	P4.3	16	P4.3	A1	P4.3

Notes: Pins 11, 15, 26, and 27 are No Connects (NC) on the 48-pin TQFP.

Descriptions of the Power pins are as follows:

VDDD: Power supply for the digital section. VDDA: Power supply for the analog section.

VSSD, VSSA: Ground pins for the digital and analog sections respectively.

VCCD: Regulated digital supply (1.8 V \pm 5%) VDD: Power supply to all sections of the chip VSS: Ground for all sections of the chip



PSoC[®] 4: PSoC 4100S Family Datasheet

Port/Pin	Analog	Smart I/O	Alternate Function 1	Alternate Function 2	Alternate Function 3	Deep Sleep 1	Deep Sleep 2
P2.4	sarmux[4]	prgio[0].io[4]	tcpwm.line[0]:1				scb[1].spi_select1:1
P2.5	sarmux[5]	prgio[0].io[5]	tcpwm.line_compl[0]:1				scb[1].spi_select2:1
P2.6	sarmux[6]	prgio[0].io[6]	tcpwm.line[1]:1				scb[1].spi_select3:1
P2.7	sarmux[7]	prgio[0].io[7]	tcpwm.line_compl[1]:1			lpcomp.comp[0]:1	scb[2].spi_mosi
P3.0		prgio[1].io[0]	tcpwm.line[0]:0	scb[1].uart_rx:1		scb[1].i2c_scl:2	scb[1].spi_mosi:0
P3.1		prgio[1].io[1]	tcpwm.line_compl[0]:0	scb[1].uart_tx:1		scb[1].i2c_sda:2	scb[1].spi_miso:0
P3.2		prgio[1].io[2]	tcpwm.line[1]:0	scb[1].uart_cts:1		cpuss.swd_data	scb[1].spi_clk:0
P3.3		prgio[1].io[3]	tcpwm.line_compl[1]:0	scb[1].uart_rts:1		cpuss.swd_clk	scb[1].spi_select0:0
P3.4		prgio[1].io[4]	tcpwm.line[2]:0		tcpwm.tr_in[6]		scb[1].spi_select1:0
P3.5		prgio[1].io[5]	tcpwm.line_compl[2]:0				scb[1].spi_select2:0
P3.6		prgio[1].io[6]	tcpwm.line[3]:0				scb[1].spi_select3:0
P3.7		prgio[1].io[7]	tcpwm.line_compl[3]:0			lpcomp.comp[1]:1	scb[2].spi_miso
P4.0	csd.vref_ext			scb[0].uart_rx:0		scb[0].i2c_scl:1	scb[0].spi_mosi:0
P4.1	csd.cshieldpads			scb[0].uart_tx:0		scb[0].i2c_sda:1	scb[0].spi_miso:0
P4.2	csd.cmodpad			scb[0].uart_cts:0		lpcomp.comp[0]:0	scb[0].spi_clk:0
P4.3	csd.csh_tank			scb[0].uart_rts:0		lpcomp.comp[1]:0	scb[0].spi_select0:0

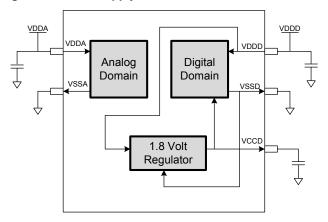
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Power

The following power system diagram shows the set of power supply pins as implemented for the PSoC 4100S. The system has one regulator in Active mode for the digital circuitry. There is no analog regulator; the analog circuits run directly from the V_{DD} input.

Figure 4. Power Supply Connections



There are two distinct modes of operation. In Mode 1, the supply voltage range is 1.8 V to 5.5 V (unregulated externally; internal regulator operational). In Mode 2, the supply range is 1.8 V ±5% (externally regulated; 1.71 to 1.89, internal regulator bypassed).

Mode 1: 1.8 V to 5.5 V External Supply

In this mode, the PSoC 4100S is powered by an external power supply that can be anywhere in the range of 1.8 to 5.5 V. This range is also designed for battery-powered operation. For example, the chip can be powered from a battery system that starts at 3.5 V and works down to 1.8 V. In this mode, the internal regulator of the PSoC 4100S supplies the internal logic and its output is connected to the $V_{\rm CCD}$ pin. The VCCD pin must be bypassed to ground via an external capacitor (0.1 μ F; X5R ceramic or better) and must not be connected to anything else.

Mode 2: 1.8 V ±5% External Supply

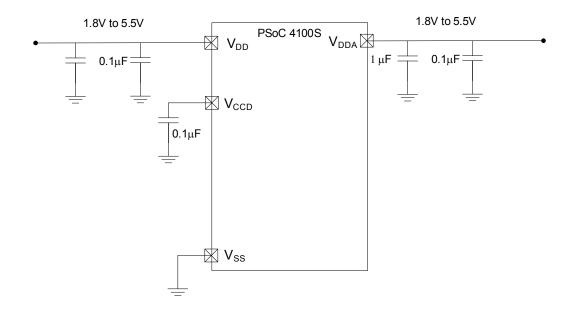
In this mode, the PSoC 4100S is powered by an external power supply that must be within the range of 1.71 to 1.89 V; note that this range needs to include the power supply ripple too. In this mode, the VDD and VCCD pins are shorted together and bypassed. The internal regulator can be disabled in the firmware.

Bypass capacitors must be used from VDDD to ground. The typical practice for systems in this frequency range is to use a capacitor in the 1- μ F range, in parallel with a smaller capacitor (0.1 μ F, for example). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

An example of a bypass scheme is shown in the following diagram.

Figure 5. External Supply Range from 1.8 V to 5.5 V with Internal Regulator Active

Power supply bypass connections example





Electrical Specifications

Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings^[1]

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID1	V _{DDD_ABS}	Digital supply relative to V _{SS}	-0.5	_	6		_
SID2	V _{CCD_ABS}	Direct digital core voltage input relative to V _{SS}	-0.5	-	1.95	V	_
SID3	V _{GPIO_ABS}	GPIO voltage	-0.5	-	V _{DD} +0.5		_
SID4	I _{GPIO_ABS}	Maximum current per GPIO	-25	-	25		_
SID5	GPIO_injection	GPIO injection current, Max for $V_{IH} > V_{DDD}$, and Min for $V_{IL} < V_{SS}$	-0.5	-	0.5	mA	Current injected per pin
BID44	ESD_HBM	Electrostatic discharge human body model	2200	_	_	V	-
BID45	ESD_CDM	Electrostatic discharge charged device model	500	-	_	V	-
BID46	LU	Pin current for latch-up	-140	-	140	mA	_

Device Level Specifications

All specifications are valid for $-40~^{\circ}\text{C} \le T_A \le 85~^{\circ}\text{C}$ and $T_J \le 100~^{\circ}\text{C}$, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 3. DC Specifications

Typical values measured at V_{DD} = 3.3 V and 25 °C.

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID53	V_{DD}	Power supply input voltage	1.8	_	5.5		Internally regulated supply
SID255	V_{DD}	Power supply input voltage ($V_{CCD} = V_{DDD} = V_{DDA}$)	1.71	-	1.89	V	Internally unregulated supply
SID54	V_{CCD}	Output voltage (for core logic)	-	1.8	-		_
SID55	C _{EFC}	External regulator voltage bypass	_	0.1	_	μF	X5R ceramic or better
SID56	C _{EXC}	Power supply bypass capacitor	_	1	_	μι	X5R ceramic or better
Active Mode, V	/ _{DD} = 1.8 V to 5	.5 V. Typical values measured at VDD	= 3.3 V and	d 25 °C.			
SID10	I _{DD5}	Execute from flash; CPU at 6 MHz	-	1.8	2.7		Max is at 85 °C and 5.5 V
SID16	I _{DD8}	Execute from flash; CPU at 24 MHz	_	3.0	4.75	mA	Max is at 85 °C and 5.5 V
SID19	I _{DD11}	Execute from flash; CPU at 48 MHz	_	5.4	6.85		Max is at 85 °C and 5.5 V

Note

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^{1.} Usage above the absolute maximum conditions listed in Table 2 may cause permanent damage to the device. Exposure to Absolute Maximum conditions for extended periods of time may affect device reliability. The Maximum Storage Temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below Absolute Maximum conditions but above normal operating conditions, the device may not operate to specification.



Table 3. DC Specifications (continued)

Typical values measured at V_{DD} = 3.3 V and 25 °C.

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
Sleep Mode,	VDDD = 1.8 V to	5.5 V (Regulator on)					
SID22	IDD17	I ² C wakeup WDT, and Comparators on	_	1.7	2.2	mA	6 MHZ. Max is at 85 °C and 5.5 V.
SID25	IDD20	I ² C wakeup, WDT, and Comparators on.	_	2.2	2.5		12 MHZ. Max is at 85 °C and 5.5 V.
Sleep Mode,	V _{DDD} = 1.71 V to	o 1.89 V (Regulator bypassed)				· •	
SID28	IDD23	I ² C wakeup, WDT, and Comparators on	_	0.7	0.9	mA	6 MHZ. Max is at 85 °C and 5.5 V.
SID28A	IDD23A	I ² C wakeup, WDT, and Comparators on	_	1	1.2	mA	12 MHZ. Max is at 85 °C and 5.5 V.
Deep Sleep	Mode, V _{DD} = 1.8	V to 3.6 V (Regulator on)		•			
SID31	I _{DD26}	I ² C wakeup and WDT on	_	2.5	60	μA	Max is at 3.6 V and 85 °C.
Deep Sleep	Mode, V _{DD} = 3.6	V to 5.5 V (Regulator on)				1	
SID34	I _{DD29}	I ² C wakeup and WDT on	_	2.5	60	μА	Max is at 5.5 V and 85 °C.
Deep Sleep	Mode, V _{DD} = V _{CO}	_{CD} = 1.71 V to 1.89 V (Regulator bypasse	ed)			1	
SID37	I _{DD32}	I ² C wakeup and WDT on	_	2.5	65	μΑ	Max is at 1.89 V and 85 °C.
XRES Curre	nt			•		•	
SID307	I _{DD_XR}	Supply current while XRES asserted	_	2	5	mA	_

Table 4. AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID48	F _{CPU}	CPU frequency	DC	_	48	MHz	$1.71 \le V_{DD} \le 5.5$
SID49 ^[3]	T _{SLEEP}	Wakeup from Sleep mode	_	0	_	us	
SID50 ^[3]	T _{DEEPSLEEP}	Wakeup from Deep Sleep mode	_	35	1	μδ	

Note
2. Guaranteed by characterization.



GPIO

Table 5. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID57	V _{IH} [3]	Input voltage high threshold	$0.7 \times V_{DDD}$	-	_		CMOS Input
SID58	V _{IL}	Input voltage low threshold	-	_	$0.3 \times V_{DDD}$		CMOS Input
SID241	V _{IH} [3]	LVTTL input, V _{DDD} < 2.7 V	$0.7 \times V_{DDD}$	-	_		_
SID242	V _{IL}	LVTTL input, V _{DDD} < 2.7 V	-	_	$0.3 \times V_{DDD}$		_
SID243	V _{IH} [3]	LVTTL input, $V_{DDD} \ge 2.7 \text{ V}$	2.0	-	_		_
SID244	V _{IL}	LVTTL input, $V_{DDD} \ge 2.7 \text{ V}$	_	-	8.0	V	_
SID59	V _{OH}	Output voltage high level	V _{DDD} -0.6	-	_		I_{OH} = 4 mA at 3 V V_{DDD}
SID60	V _{OH}	Output voltage high level	V _{DDD} -0.5	-	_		I _{OH} = 1 mA at 1.8 V V _{DDD}
SID61	V _{OL}	Output voltage low level	-	_	0.6		I _{OL} = 4 mA at 1.8 V V _{DDD}
SID62	V _{OL}	Output voltage low level	_	-	0.6		I_{OL} = 10 mA at 3 V V_{DDD}
SID62A	V _{OL}	Output voltage low level	-	-	0.4		I_{OL} = 3 mA at 3 V V_{DDD}
SID63	R _{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	_
SID64	R _{PULLDOWN}	Pull-down resistor	3.5	5.6	8.5	N22	_
SID65	I _{IL}	Input leakage current (absolute value)	_	_	2	nA	25 °C, V _{DDD} = 3.0 V
SID66	C _{IN}	Input capacitance	_	-	7	pF	_
SID67 ^[4]	V _{HYSTTL}	Input hysteresis LVTTL	25	40	_		$V_{DDD} \ge 2.7 \text{ V}$
SID68 ^[4]	V _{HYSCMOS}	Input hysteresis CMOS	$0.05 \times V_{DDD}$	-	_	mV	V _{DD} < 4.5 V
SID68A ^[4]	V _{HYSCMOS5V5}	Input hysteresis CMOS	200	-	_		V _{DD} > 4.5 V
SID69 ^[4]	I _{DIODE}	Current through protection diode to V_{DD}/V_{SS}	-	_	100	μA	_
SID69A ^[4]	I _{TOT_GPIO}	Maximum total source or sink chip current	_	_	200	mA	-

Table 6. GPIO AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID70	T _{RISEF}	Rise time in fast strong mode	2	1	12		3.3 V V _{DDD} , Cload = 25 pF
SID71	T _{FALLF}	Fall time in fast strong mode	2	_	12		3.3 V V _{DDD} , Cload = 25 pF
SID72	T _{RISES}	Rise time in slow strong mode	10	_	60		3.3 V V _{DDD} , Cload = 25 pF

V_{IH} must not exceed V_{DDD} + 0.2 V.
 Guaranteed by characterization.



Table 9. CTBm Opamp Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
		General opamp specs for both internal and external modes					
SID281	V _{IN}	Charge-pump on, $V_{DDA} = 2.7 \text{ V}$	-0.05	-	V _{DDA} -0.2	V	_
SID282	V _{CM}	Charge-pump on, V _{DDA} = 2.7 V	-0.05	_	V _{DDA} -0.2		_
	V _{OUT}	V _{DDA} = 2.7 V		l	•		,
SID283	V _{OUT_1}	power=hi, Iload=10 mA	0.5	_	V _{DDA} -0.5		_
SID284	V _{OUT_2}	power=hi, Iload=1 mA	0.2	_	V _{DDA} -0.2	V	_
SID285	V _{OUT_3}	power=med, Iload=1 mA	0.2	_	V _{DDA} -0.2	v	_
SID286	V _{OUT_4}	power=lo, Iload=0.1 mA	0.2	_	V _{DDA} -0.2		_
SID288	V _{OS_TR}	Offset voltage, trimmed	-1.0	±0.5	1.0		High mode, input 0 V to V _{DDA} -0.2 V
SID288A	V _{OS_TR}	Offset voltage, trimmed	_	±1	_	mV	Medium mode, input 0 V to V _{DDA} -0.2 V
SID288B	V _{OS_TR}	Offset voltage, trimmed	-	±2	_		Low mode, input 0 V to V _{DDA} -0.2 V
SID290	V _{OS_DR_TR}	Offset voltage drift, trimmed	-10	±3	10	μV/C	High mode
SID290A	V _{OS_DR_TR}	Offset voltage drift, trimmed	-	±10	_	μV/C	Medium mode
SID290B	V _{OS_DR_TR}	Offset voltage drift, trimmed	_	±10	_	μν/Ο	Low mode
SID291	CMRR	DC	70	80	_		Input is 0 V to V _{DDA} -0.2 V, Output is 0.2 V to V _{DDA} -0.2 V
SID292	PSRR	At 1 kHz, 10-mV ripple	70	85	-	dB	V _{DDD} = 3.6 V, high-power mode, input is 0.2 V to V _{DDA} -0.2 V
	Noise						
SID294	VN2	Input-referred, 1 kHz, power=Hi	_	72	_		3
SID295	VN3	Input-referred, 10 kHz, power=Hi	-	28	_	nV/rtHz	Input and output are at 0.2 V to V _{DDA} -0.2 V
SID296	VN4	Input-referred, 100 kHz, power=Hi	-	15	_		Input and output are at 0.2 V to V _{DDA} -0.2 V
SID297	C _{LOAD}	Stable up to max. load. Performance specs at 50 pF.	-	-	125	pF	-
SID298	SLEW_RATE	Cload = 50 pF, Power = High, V _{DDA} = 2.7 V	6	-	_	V/µs	_



Table 9. CTBm Opamp Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID_DS_7	G _{BW_HI_M1}	Mode 1, High current	-	4	-		20-pF load, no DC load 0.2 V to V _{DDA} -0.2 V
SID_DS_8	G _{BW_MED_M1}	Mode 1, Medium current	_	2	Ι		20-pF load, no DC load 0.2 V to V _{DDA} -0.2 V
SID_DS_9	G _{BW_LOW_M!}	Mode 1, Low current	_	0.5	1	- MHz	20-pF load, no DC load 0.2 V to V _{DDA} -0.2 V
SID_DS_10	G _{BW_HI_M2}	Mode 2, High current	_	0.5	ı	IVITZ	20-pF load, no DC load 0.2 V to V _{DDA} -0.2 V
SID_DS_11	G _{BW_MED_M2}	Mode 2, Medium current	_	0.2	I		20-pF load, no DC load 0.2 V to V _{DDA} -0.2 V
SID_DS_12	G _{BW_Low_M2}	Mode 2, Low current	_	0.1	I		20-pF load, no DC load 0.2 V to V _{DDA} -0.2 V
SID_DS_13	V _{OS_HI_M1}	Mode 1, High current	_	5	1		With trim 25 °C, 0.2 V to V _{DDA} -0.2 V
SID_DS_14	V _{OS_MED_M1}	Mode 1, Medium current	_	5	_		With trim 25 °C, 0.2 V to V _{DDA} -0.2 V
SID_DS_15	V _{OS_LOW_M2}	Mode 1, Low current	_	5	_	>/	With trim 25 °C, 0.2 V to V _{DDA} -0.2 V
SID_DS_16	V _{OS_HI_M2}	Mode 2, High current	_	5	_	- mV	With trim 25 °C, 0.2V to V _{DDA} -0.2 V
SID_DS_17	V _{OS_MED_M2}	Mode 2, Medium current	_	5	_		With trim 25 °C, 0.2 V to V _{DDA} -0.2 V
SID_DS_18	V _{OS_LOW_M2}	Mode 2, Low current	_	5	_		With trim 25 °C, 0.2 V to V _{DDA} -0.2 V
SID_DS_19	I _{OUT_HI_M!}	Mode 1, High current	_	10	_		Output is 0.5 V to V _{DDA} -0.5 V
SID_DS_20	I _{OUT_MED_M1}	Mode 1, Medium current	_	10	_		Output is 0.5 V to V _{DDA} -0.5 V
SID_DS_21	I _{OUT_LOW_M1}	Mode 1, Low current	_	4	_		Output is 0.5 V to V _{DDA} -0.5 V
SID_DS_22	I _{OUT_HI_M2}	Mode 2, High current	_	1	-	mA	
SID_DS_23	I _{OU_MED_M2}	Mode 2, Medium current	_	1	-		
SID_DS_24	I _{OU_LOW_M2}	Mode 2, Low current	_	0.5	-		

Note6. Guaranteed by characterization.



Table 10. Comparator DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID84	V _{OFFSET1}	Input offset voltage, Factory trim	_	_	±10		
SID85	V _{OFFSET2}	Input offset voltage, Custom trim	_	_	±4	mV	
SID86	V _{HYST}	Hysteresis when enabled	_	10	35		
SID87	V _{ICM1}	Input common mode voltage in normal mode	0	_	V _{DDD} -0.1		Modes 1 and 2
SID247	V _{ICM2}	Input common mode voltage in low power mode	0	_	V_{DDD}	V	
SID247A	V _{ICM3}	Input common mode voltage in ultra low power mode	0	-	V _{DDD} -1.15	·	V _{DDD} ≥ 2.2 V at -40 °C
SID88	C _{MRR}	Common mode rejection ratio	50	_	_	dB	V _{DDD} ≥ 2.7V
SID88A	C _{MRR}	Common mode rejection ratio	42	_	-	uБ	V _{DDD} ≤ 2.7V
SID89	I _{CMP1}	Block current, normal mode	_	_	400		
SID248	I _{CMP2}	Block current, low power mode	_	_	100	μA	
SID259	I _{CMP3}	Block current in ultra low-power mode	_	-	6	F, ,	V _{DDD} ≥ 2.2 V at -40 °C
SID90	Z _{CMP}	DC Input impedance of comparator	35	_	-	ΜΩ	

Table 11. Comparator AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID91	TRESP1	Response time, normal mode, 50 mV overdrive	-	38	110		
SID258	TRESP2	Response time, low power mode, 50 mV overdrive	-	70	200	ns	
SID92	TRESP3	Response time, ultra-low power mode, 200 mV overdrive	-	2.3	15	μs	V _{DDD} ≥ 2.2 V at -40 °C

Table 12. Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
SID93	TSENSACC	Temperature sensor accuracy	- 5	±1	5	°C	–40 to +85 °C

Table 13. SAR Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SAR ADC	DC Specificati	ons					
SID94	A_RES	Resolution	_	_	12	bits	
SID95	A_CHNLS_S	Number of channels - single ended	-	_	16		
SID96	A-CHNKS_D	Number of channels - differential	_	_	4		Diff inputs use neighboring I/O
SID97	A-MONO	Monotonicity	_	_	_		Yes.
SID98	A_GAINERR	Gain error	_	_	±0.1	%	With external reference.

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Table 14. CSD and IDAC Specifications (continued)

SPEC ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
SID315G	IDAC3CRT23	Output current of IDAC in 8-bit mode in medium range	69	_	82	μA	LSB = 300-nA typ.
SID315H	IDAC3CRT33	Output current of IDAC in 8-bit mode in high range	540	_	660	μA	LSB = 2.4-µA typ.
SID320	IDACOFFSET	All zeroes input	-	-	1	LSB	Polarity set by Source or Sink. Offset is 2 LSBs for 37.5 nA/LSB mode
SID321	IDACGAIN	Full-scale error less offset	_	_	±10	%	
SID322	IDACMISMATCH1	Mismatch between IDAC1 and IDAC2 in Low mode	-	-	9.2	LSB	LSB = 37.5-nA typ.
SID322A	IDACMISMATCH2	Mismatch between IDAC1 and IDAC2 in Medium mode	-	-	5.6	LSB	LSB = 300-nA typ.
SID322B	IDACMISMATCH3	Mismatch between IDAC1 and IDAC2 in High mode	-	-	6.8	LSB	LSB = 2.4-µA typ.
SID323	IDACSET8	Settling time to 0.5 LSB for 8-bit IDAC	-	-	10	μs	Full-scale transition. No external load.
SID324	IDACSET7	Settling time to 0.5 LSB for 7-bit IDAC	_	-	10	μs	Full-scale transition. No external load.
SID325	CMOD	External modulator capacitor.	-	2.2	_	nF	5-V rating, X7R or NP0 cap.

Table 15. 10-bit CapSense ADC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SIDA94	A_RES	Resolution	_	_	10	bits	Auto-zeroing is required every millisecond
SIDA95	A_CHNLS_S	Number of channels - single ended	_	-	16		Defined by AMUX Bus.
SIDA97	A-MONO	Monotonicity	_	_	_	Yes	
SIDA98	A_GAINERR	Gain error	-	_	±2	%	In V _{REF} (2.4 V) mode with V _{DDA} bypass capacitance of 10 µF
SIDA99	A_OFFSET	Input offset voltage	-	-	3	mV	In V _{REF} (2.4 V) mode with V _{DDA} bypass capacitance of 10 µF
SIDA100	A_ISAR	Current consumption	_	_	0.25	mΑ	
SIDA101	A_VINS	Input voltage range - single ended	V_{SSA}	_	V_{DDA}	V	
SIDA103	A_INRES	Input resistance	_	2.2	-	ΚΩ	
SIDA104	A_INCAP	Input capacitance	_	20	-	pF	
SIDA106	A_PSRR	Power supply rejection ratio	-	60	_	dB	In V _{REF} (2.4 V) mode with V _{DDA} bypass capacitance of 10 µF
SIDA107	A_TACQ	Sample acquisition time	_	1	-	μs	
SIDA108	A_CONV8	Conversion time for 8-bit resolution at conversion rate = Fhclk/(2^(N+2)). Clock frequency = 48 MHz.	_	_	21.3	μs	Does not include acquisition time. Equivalent to 44.8 ksps including acquisition time.
SIDA108A	A_CONV10	Conversion time for 10-bit resolution at conversion rate = Fhclk/(2^(N+2)). Clock frequency = 48 MHz.	_	_	85.3	μs	Does not include acquisition time. Equivalent to 11.6 ksps including acquisition time.

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Table 19. SPI DC Specifications $^{[9]}$

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID163	ISPI1	Block current consumption at 1 Mbps	-	_	360		_
SID164	ISPI2	Block current consumption at 4 Mbps	-	_	560	μA	_
SID165	ISPI3	Block current consumption at 8 Mbps	_	_	600		-

Table 20. SPI AC Specifications^[8]

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions				
SID166	FSPI	SPI Operating frequency (Master; 6X Oversampling)	-	_	8	MHz	SID166				
Fixed SPI	Fixed SPI Master Mode AC Specifications										
SID167	TDMO	MOSI Valid after SClock driving edge	_	_	15		_				
SID168	TDSI	MISO Valid before SClock capturing edge	20	_	_	ns	Full clock, late MISO sampling				
SID169	тнмо	Previous MOSI data hold time	0	_	_		Referred to Slave capturing edge				
Fixed SPI	Slave Mode AC	Specifications									
SID170	TDMI	MOSI Valid before Sclock Capturing edge	40	_	_		-				
SID171	TDSO	MISO Valid after Sclock driving edge	-	_	42 + 3*Tcpu	ns	T _{CPU} = 1/F _{CPU}				
SID171A	TDSO_EXT	MISO Valid after Sclock driving edge in Ext. Clk mode	_	_	48		-				
SID172	THSO	Previous MISO data hold time	0	_	_		_				
SID172A	TSSELSSCK	SSEL Valid to first SCK Valid edge	-	_	100	ns	-				

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Memory

Table 25. Flash DC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID173	V_{PE}	Erase and program voltage	1.71	1	5.5	V	_

Table 26. Flash AC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID174	T _{ROWWRITE} ^[10]	Row (block) write time (erase and program)	-	-	20		Row (block) = 128 bytes
SID175	T _{ROWERASE} ^[10]	Row erase time	-	_	16	ms	_
SID176	T _{ROWPROGRAM} ^[10]	Row program time after erase	-	_	4		-
SID178	T _{BULKERASE} ^[10]	Bulk erase time (64 KB)	_	-	35		_
SID180 ^[11]	T _{DEVPROG} ^[10]	Total device program time	_	_	7	Seconds	-
SID181 ^[11]	F _{END}	Flash endurance	100 K	_	_	Cycles	-
SID182 ^[11]	F _{RET}	Flash retention. $T_A \le 55$ °C, 100 K P/E cycles	20	_	-	Years	-
SID182A ^[11]	_	Flash retention. $T_A \le 85$ °C, 10 K P/E cycles	10	-	_	Tears	-
SID256	TWS48	Number of Wait states at 48 MHz	2	-	_		CPU execution from Flash
SID257	TWS24	Number of Wait states at 24 MHz	1	_	_		CPU execution from Flash

System Resources

Power-on Reset (POR)

Table 27. Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID.CLK#6	SR_POWER_UP	Power supply slew rate	1	1	67	V/ms	At power-up
SID185 ^[11]	V _{RISEIPOR}	Rising trip voltage	0.80	1	1.5	V	_
SID186 ^[11]	V _{FALLIPOR}	Falling trip voltage	0.70	-	1.4		_

Table 28. Brown-out Detect (BOD) for $V_{\mbox{\scriptsize CCD}}$

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID190 ^[11]	V _{FALLPPOR}	BOD trip voltage in active and sleep modes	1.48	1	1.62	V	-
SID192 ^[11]	V _{FALLDPSLP}	BOD trip voltage in Deep Sleep	1.11	-	1.5		_

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Notes

10. It can take as much as 20 milliseconds to write to Flash. During this time the device should not be Reset, or Flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.



Ordering Information

The marketing part numbers for the PSoC 4100S family are listed in the following table.

	Features										Package								
Category	MPN	Max CPU Speed (MHz)	Flash (KB)	SRAM (KB)	Opamp (CTBm)	CSD	10-bit CSD ADC	12-bit SAR ADC	ADC Sample Rate	LP Comparators	TCPWM Blocks	SCB Blocks	Smart I/Os	GPIO	35-WLCSP (0.35mm pitch)	32-QFN	40-QFN	48-TQFP	44-TQFP
	CY8C4124FNI-S403	24	16	4	2	0	1	0		2	5	2	8	31	Χ				
	CY8C4124FNI-S413	24	16	4	2	1	1	0		2	5	2	16	31	Х				
	CY8C4124LQI-S412	24	16	4	2	1	1	0		2	5	2	16	27		Х			
	CY8C4124LQI-S413	24	16	4	2	1	1	0		2	5	2	16	34			Х		
4124	CY8C4124AZI-S413	24	16	4	2	1	1	0		2	5	2	16	36				Х	
	CY8C4124FNI-S433	24	16	4	2	1	1	1	806 ksps	2	5	2	16	31	Х				
	CY8C4124LQI-S432	24	16	4	2	1	1	1	806 ksps	2	5	2	16	27		Х			
	CY8C4124LQI-S433	24	16	4	2	1	1	1	806 ksps	2	5	2	16	34			Х		
	CY8C4124AZI-S433	24	16	4	2	1	1	1	806 ksps	2	5	2	16	36				Х	
	CY8C4125FNI-S423	24	32	4	2	0	1	1	806 ksps	2	5	2	16	31	Х				
	CY8C4125LQI-S422	24	32	4	2	0	1	1	806 ksps	2	5	2	16	27		Х			
-	CY8C4125LQI-S423	24	32	4	2	0	1	1	806 ksps	2	5	2	16	34			Х		
-	CY8C4125AZI-S423	24	32	4	2	0	1	1	806 ksps	2	5	2	16	36				Х	
-	CY8C4125AXI-S423	24	32	4	2	0	1	1	806 ksps	2	5	2	16	36					Х
-	CY8C4125FNI-S413	24	32	4	2	1	1	0		2	5	2	16	31	Х				
	CY8C4125LQI-S412	24	32	4	2	1	1	0		2	5	2	16	27		Х			
4125	CY8C4125LQI-S413	24	32	4	2	1	1	0		2	5	2	16	34			Х		
-	CY8C4125AZI-S413	24	32	4	2	1	1	0		2	5	2	16	36				Х	
	CY8C4125FNI-S433	24	32	4	2	1	1	1	806 ksps	2	5	2	16	31	Х				
	CY8C4125LQI-S432	24	32	4	2	1	1	1	806 ksps	2	5	2	16	27		Х			
	CY8C4125LQI-S433	24	32	4	2	1	1	1	806 ksps	2	5	2	16	34			Х		
	CY8C4125AZI-S433	24	32	4	2	1	1	1	806 ksps	2	5	2	16	36				Х	
	CY8C4125AXI-S433	24	32	4	2	1	1	1	806 ksps	2	5	2	16	36					Х
	CY8C4126AZI-S423	24	64	8	2	0	1	1	806 ksps	2	5	3	16	36				Х	
	CY8C4126AXI-S423	24	64	8	2	0	1	1	806 ksps	2	5	3	16	36					Х
4126	CY8C4126AZI-S433	24	64	8	2	1	1	1	806 ksps	2	5	3	16	36				Х	
	CY8C4126AXI-S433	24	64	8	2	1	1	1	806 ksps	2	5	3	16	36					Х
	CY8C4145AZI-S423	48	32	4	2	0	1	1	1 Msps	2	5	2	16	36				Х	
4145	CY8C4145AXI-S423	48	32	4	2	0	1	1	1 Msps	2	5	2	16	36					Х
	CY8C4145AXI-S433	48	32	4	2	1	1	1	1 Msps	2	5	2	16	36					Х
	CY8C4146FNI-S423	48	64	8	2	0	1	1	1 Msps	2	5	3	16	31	Х				
	CY8C4146LQI-S422	48	64	8	2	0	1	1	1 Msps	2	5	3	16	27		Х			
	CY8C4146LQI-S423	48	64	8	2	0	1	1	1 Msps	2	5	3	16	34			Х		\vdash
	CY8C4146AZI-S423	48	64	8	2	0	1	1	1 Msps	2	5	3	16	36				Х	
14.5	CY8C4146AXI-S423	48	64	8	2	0	1	1	1 Msps	2	5	3	16	36					Х
4146	CY8C4146FNI-S433	48	64	8	2	1	1	1	1 Msps	2	5	3	16	31	Х				
	CY8C4146LQI-S432	48	64	8	2	1	1	1	1 Msps	2	5	3	16	27		Х			\vdash
	CY8C4146LQI-S433	48	64	8	2	1	1	1	1 Msps	2	5	3	16	34			Х		\vdash
	CY8C4146AZI-S433	48	64	8	2	1	1	1	1 Msps	2	5	3	16	36				Х	\vdash
	CY8C4146AXI-S433	48	64	8	2	1	1	1	1 Msps	2	5	3	16	36					Х



The nomenclature used in the preceding table is based on the following part numbering convention:

Field	Description	Values	Meaning
CY8C	Cypress Prefix		
4	Architecture	4	PSoC 4
Α	Family	1	4100 Family
В	CPU Speed	2	24 MHz
		4	48 MHz
С	Flash Capacity	4	16 KB
		5	32 KB
		6	64 KB
		7	128 KB
DE	Package Code	AX	TQFP (0.8mm pitch)
		AZ	TQFP (0.5mm pitch)
		LQ	QFN
		PV	SSOP
		FN	CSP
F	Temperature Range	I	Industrial
S	Silicon Family	S	PSoC 4A-S1, PSoC 4A-S2
		М	PSoC 4A-M
		L	PSoC 4A-L
		BL	PSoC 4A-BLE
XYZ	Attributes Code	000-999	Code of feature set in the specific family

The following is an example of a part number:

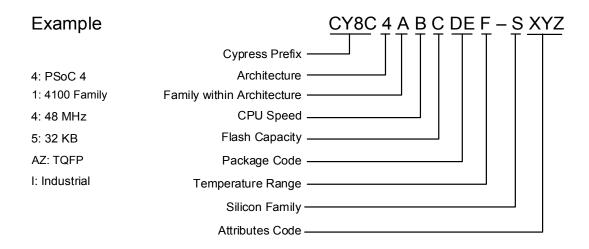




Table 42. Acronyms Used in this Document (continued)

Acronym	Description
PC	program counter
PCB	printed circuit board
PGA	programmable gain amplifier
PHUB	peripheral hub
PHY	physical layer
PICU	port interrupt control unit
PLA	programmable logic array
PLD	programmable logic device, see also PAL
PLL	phase-locked loop
PMDD	package material declaration data sheet
POR	power-on reset
PRES	precise power-on reset
PRS	pseudo random sequence
PS	port read data register
PSoC [®]	Programmable System-on-Chip™
PSRR	power supply rejection ratio
PWM	pulse-width modulator
RAM	random-access memory
RISC	reduced-instruction-set computing
RMS	root-mean-square
RTC	real-time clock
RTL	register transfer language
RTR	remote transmission request
RX	receive
SAR	successive approximation register
SC/CT	switched capacitor/continuous time
SCL	I ² C serial clock
SDA	I ² C serial data
S/H	sample and hold
SINAD	signal to noise and distortion ratio
SIO	special input/output, GPIO with advanced features. See GPIO.
SOC	start of conversion
SOF	start of frame
SPI	Serial Peripheral Interface, a communications protocol
SR	slew rate
SRAM	static random access memory
SRES	software reset
SWD	serial wire debug, a test protocol

Table 42. Acronyms Used in this Document (continued)

Acronym	Description
SWV	single-wire viewer
TD	transaction descriptor, see also DMA
THD	total harmonic distortion
TIA	transimpedance amplifier
TRM	technical reference manual
TTL	transistor-transistor logic
TX	transmit
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
UDB	universal digital block
USB	Universal Serial Bus
USBIO	USB input/output, PSoC pins used to connect to a USB port
VDAC	voltage DAC, see also DAC, IDAC
WDT	watchdog timer
WOL	write once latch, see also NVL
WRES	watchdog timer reset
XRES	external reset I/O pin
XTAL	crystal

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Document Conventions

Units of Measure

Table 43. Units of Measure

Table 43. Units of Measure					
Symbol	Unit of Measure				
°C	degrees Celsius				
dB	decibel				
fF	femto farad				
Hz	hertz				
KB	1024 bytes				
kbps	kilobits per second				
Khr	kilohour				
kHz	kilohertz				
kΩ	kilo ohm				
ksps	kilosamples per second				
LSB	least significant bit				
Mbps	megabits per second				
MHz	megahertz				
ΜΩ	mega-ohm				
Msps	megasamples per second				
μΑ	microampere				
μF	microfarad				
μH	microhenry				
μs	microsecond				
μV	microvolt				
μW	microwatt				
mA	milliampere				
ms	millisecond				
mV	millivolt				
nA	nanoampere				
ns	nanosecond				
nV	nanovolt				
Ω	ohm				
pF	picofarad				
ppm	parts per million				
ps	picosecond				
S	second				
sps	samples per second				
sqrtHz	square root of hertz				
V	volt				



Revision History

Revision	ECN	Orig. of Change	Submission Date	Description of Change
**	4883809	WKA	08/28/2015	New datasheet
*A	4992376	WKA	10/30/2015	Updated Pinouts. Added $V_{DDD} \ge 2.2V$ at $-40~^{\circ}C$ under Conditions for specs SID247A, SID90, SID92. Updated Table 15. Updated Ordering Information.
*B	5037826	SLAN	12/08/2015	Changed datasheet status to Preliminary
*C	5060691	WKA	12/22/2015	Updated SCBs from 2 to 3. Updated SRAM size to 8 KB. Changed WLCSP package to 35-ball WLCSP. Updated Pin List and Alternate Pin Functions. Updated Ordering Information.
*D	5139206	WKA	02/16/2016	Added Errata. Added 35 WLCSP package details. Updated theta J_A and J_C values for all packages. Updated copyright information at the end of the document.
*E	5173961	WKA	03/15/2016	Updated values for SID79, BID194. SID175, and SID176. Updated CSD and IDAC Specifications. Updated 10-bit CapSense ADC Specifications.
*F	5330930	WKA	07/27/2016	Updated CSD and IDAC Specifications. Updated 10-bit CapSense ADC Specifications. Removed errata.
*G	5473409	WKA	10/13/2016	Added 44 TQFP pin and package details.
*H	5561833	WKA	01/09/2017	Updated Figure 3. Changed PRGIO references to Smart I/O. Updated DC Specifications. Updated Ordering Information.

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